

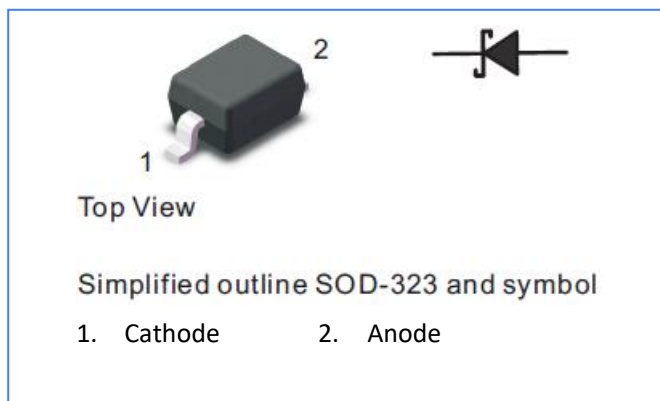
Schottky Barrier Diode

FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Negligible Reverse Recovery Time
- Low Capacitance

MECHANICAL DATA

- Case: SOD-323
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 5.48mg / 0.00019oz



Maximum Ratings and Electrical characteristics

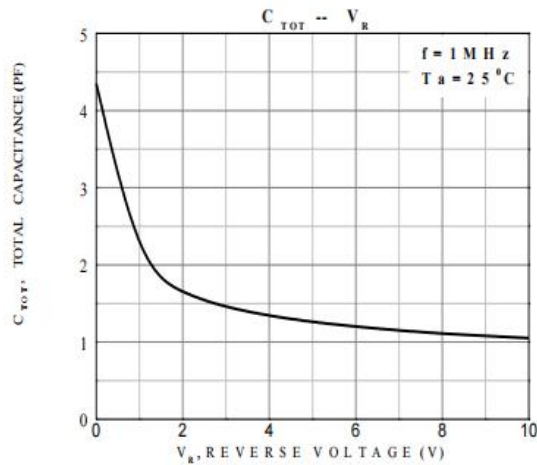
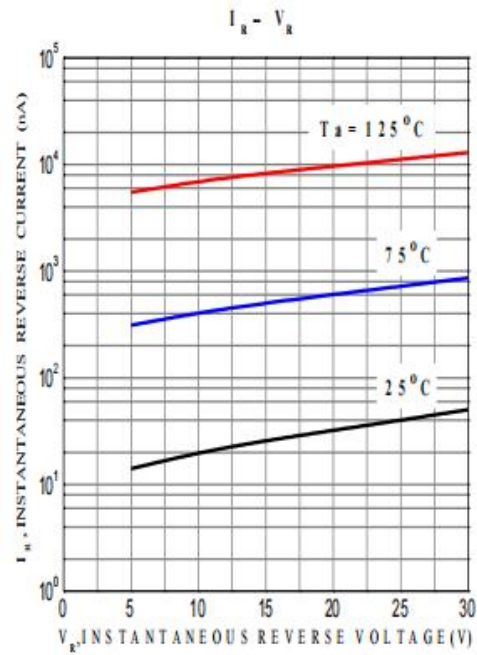
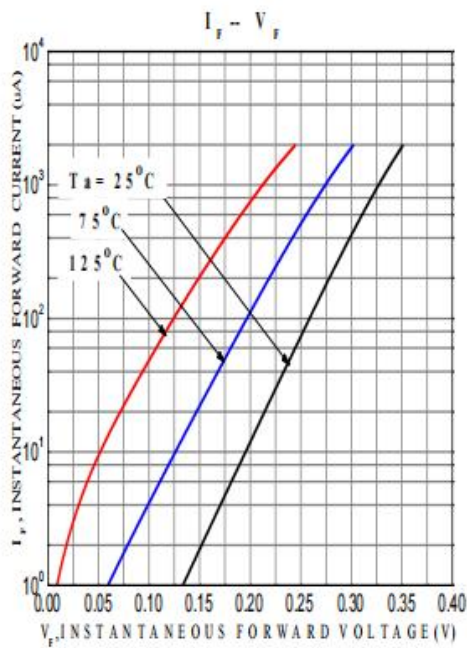
Ratings at ambient temperature unless o 25 °C therwise specified.

Symbol	Parameter	Value	Units
V_{RRM}	Peak Repetive Reverse Voltage	40	V
I_o	Mean Rectifying Current	100	mA
V_R	Peak Forward Surge Current	40	V
IFSM	Forward Continuous Current	200	mA
P_d	Peak Forward Surge Current @ $t < 1.0s$	600	mA
T_J	Junction Temperature	110	°C
T_{STG}	Storage Temperature	-40~150	°C

Electrical Characteristics Ratings at 25°C ambient temperature unless otherwise specified

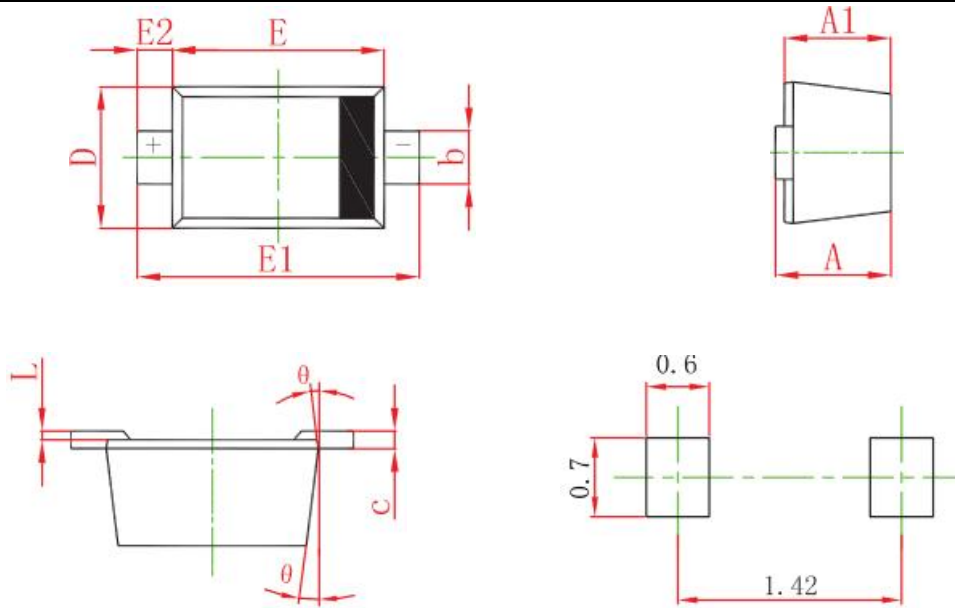
Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	V (BR)	40			V	$I_R = 100\mu A$
Forward voltage	VF1			0.38	V	$I_F = 1mA$
	VF2			0.50	V	$I_F = 10mA$
	VF3			1	V	$I_F = 40mA$
Reverse current	I_R			1	μA	$V_R = 30V$
Reverse current	I_R			10	μA	$V_R = 40V$
Capacitance between terminals	CT		4	5	pF	$V_R = 0V, f = 1MHz$
Reverse recovery time	t_{rr}			5	ns	$I_F = I_R = 10mA$ $I_{rr} = 0.1 \times I_R, R_L = 100\Omega$

Typical Characteristics



Package Dimensions

Symbol	Dimensions in mm		Dimensions in inches	
	min	max	min	max
A	0.510	0.770	0.020	0.031
A1	0.500	0.700	0.020	0.028
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	0.750	0.850	0.030	0.033
E	1.100	1.300	0.043	0.051
E1	1.500	1.700	0.059	0.067
E2	0.200REF		0.008	
L	0.010	0.070	0.001	0.003
θ	7° REF		7° REF	



Disclaimer

Specifications are subject to change without notice.

The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.

Users should verify actual device performance in their specific applications.